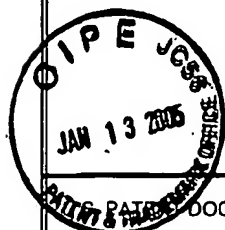


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PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
MI22-2194SERIAL NO.
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DOMESTIC PATENT DOCUMENTS

*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ							
	AK							
	AL							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

EF	AM		S.M. George, "Atomic layer controlled deposition of SiO ₂ and Al ₂ O ₃ using ABAB...binary reaction sequence chemistry", <i>Elsevier Science B.V., Applied Surface Science</i> 82/83, 1994, p. 460-467.
	AN		
	AO		

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U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
EF	AA	6,495,436	12/17/2002	Ahn et al.			
	AB	6,762,114	7/13/2004	Chambers			
	AC	6,717,226	4/6/2004	Hedge et al.			
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EF	AJ	2001/0024860	9/27/2001	Park et al.			
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FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
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EF	AR		"Surface preparation and post thermal treatment effects on interface properties of thin Al_2O_3 films deposited by ALD;" Chang et al.; Microelectronic Engineering 72, 2004; pp. 326-331.					
EF	AS		"Effect Purge time on the properties of HfO_2 films prepared by atomic layer deposition;" Kawahara et al.; IEEEJ Transactions on Electronics; Vol. E87-C, No. 1; January 2004; pp. 2-8.					
EF	AT		"High-k materials for advanced gate stack dielectrics: a comparison of ALD and MOCVD as deposition technologies;" Caymax et al.; CMOS Front-End materials and Process Technology Symposium (Mater. Res. Soc. Symposium Proceedings Vol. 765); April 22-24, 2003; 47-58					

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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

NONCONVARIANT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
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	AP							
	AQ							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

EF	AR	"Effect of Hf sources, oxidizing agents, and NH ₃ /Ar plasma on the properties of HfAlO ₃ films prepared by atomic layer deposition;" Kawahara et al.; Japanese Journal of Applied Physics, Vol. 43, No. 7A; July 2004; pp. 4129-4134.
EF	AS	"Characterization of ultra-thin HfO ₂ gate oxide prepared by using atomic layer deposition;" Tacho et al.; Journal of the Korean Physical Society, Vol. 42, No. 2; February 2003; pp. 272-273.
	AT	

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